

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

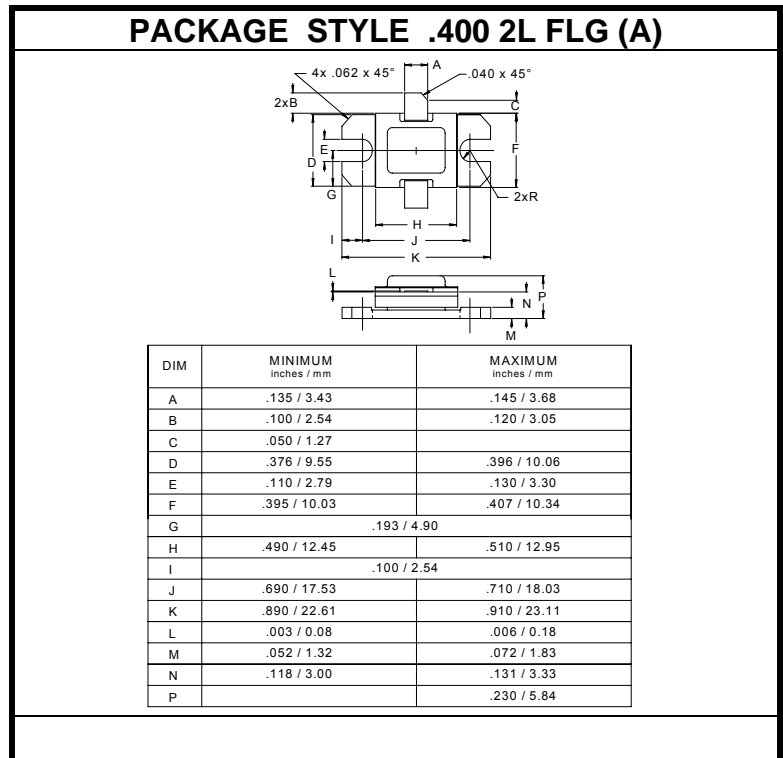
The **ASI AM1011-075** is a high power Class C transistor designed for L-Band Avionics pulse output and driver applications.

**FEATURES:**

- Internal Input/Output Matching Networks
- $P_G = 9.2$  dB min. at 75 W/1090 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	5.4 A
$V_{CC}$	55 V
$P_{DISS}$	175 W @ $T_C = 25^\circ C$
$T_J$	-65 °C to +250 °C
$T_{STG}$	-65 °C to +200 °C
$\theta_{JC}$	0.86 °C/W


**CHARACTERISTICS**  $T_C = 25^\circ C$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 50$ mA	65			V
$BV_{CER}$	$I_C = 50$ mA $R_{BE} = 10 \Omega$	65			V
$BV_{EBO}$	$I_E = 4.0$ mA	3.5			V
$I_{CES}$	$V_{CE} = 50$ V			6.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 1.0$ A	10			---
$P_G$	$V_{CC} = 50$ V $P_{IN} = 9.0$ W $f = 1090$ MHz	9.2	9.7		dB
$\eta_c$		48	56		%

Pulse Width = 32  $\mu$ sec, Duty Cycle = 2%